



Atty. Dkt. No. 016907-1577

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hitoshi TSUNO

Title: SEMICONDUCTOR DEVICE INCLUDING MOS FIELD EFFECT
TRANSISTOR HAVING OFFSET SPACERS OR GATE
SIDEWALL FILMS ON EITHER SIDE OF GATE ELECTRODE
AND METHOD OF MANUFACTURING THE SAME

Appl. No.: 10/676,264

Filing Date: 10/02/2003

Examiner: Unassigned

Art Unit: 2811

PRELIMINARY AMENDMENT UNDER 37 CFR 1.115

Mail Stop MISSING PARTS
Commissioner for Patents
PO Box 1450
Alexandria, Virginia 22313-1450

Sir:

Prior to examination of the present Application, Applicant respectfully requests that the application be amended as follows:

Amendments to the Specification begin on page 2 of this document.

Remarks/Arguments begin on page 3 of this document.

Please amend the application as follows: